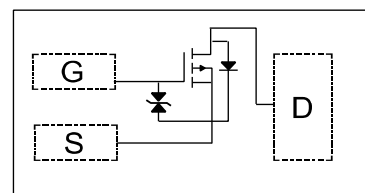


Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary

$V_{DS}(V)$	$R_{DS(on)}(\Omega)$	$I_D(mA)$
-20	0.45@ $V_{GS}=-4.5V$	-800
	0.62@ $V_{GS}=-2.5V$	
	0.86@ $V_{GS}=-1.8V$	



Top View

Absolute maximum rating@25°C

Parameter		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±10	V
Continuous Drain Current	Continuous	I_D	-800	mA
	Pulsed	I_{DP}	-1200	
Maximum Power Dissipation (Note 1)(Note 4)	$T_A=25^{\circ}C$	P_D	270	mW
	$T_A=70^{\circ}C$		170	
Maximum Power Dissipation (Note 2)(Note 4)	$T_A=25^{\circ}C$	P_D	240	mW
	$T_A=70^{\circ}C$		150	
Pulsed Drain Current(Note 3)		I_{DM}	-1.2	A
Operating Junction Temperature		T_J	150	°C
Lead Temperature		T_L	260	°C
Storage Temperature Range		T_{stg}	-55 to +150	°C

Thermal resistance

Parameter		Symbol	Min.	Typ.	Max.	Units
Junction-to-Ambient Thermal Resistance (Note 1)	$t \leq 10\text{ s}$	$R_{\theta JA}$	-	350	400	°C/W
	Steady State		-	395	460	°C/W
Junction-to-Ambient Thermal Resistance (Note 2)	$t \leq 10\text{ s}$	$R_{\theta JA}$	-	390	445	°C/W
	Steady State		-	450	515	°C/W
Junction-to-Case Thermal Resistance		$R_{\theta JA}$	-	245	290	°C/W

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	I _D =-250uA,V _{GS} =0V	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V,V _{GS} =0V	-	-	-1	μA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V,V _{GS} =±8V	-	-	±10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = -250uA	-0.45	-0.55	-0.95	V
Drain-to-source On-resistance (Note 5)	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-700mA	-	450	700	mΩ
		V _{GS} =-2.5V, I _D =-300mA	-	620	850	mΩ
		V _{GS} =-1.8V, I _D =-100mA	-	1000	1500	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-450mA	-	1.25	-	s
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-10V, f=1MHz	-	72	-	pF
Output Capacitance	C _{OSS}		-	9.5	-	pF
Reverse Transfer Capacitance	C _{RSS}		-	9.8	-	pF
Total Gate Charge	Q _{G(TOT)}	V _{GS} =-4.5V,V _{DS} =-10V, I _D =-450mA	-	0.9	-	nC
Threshold Gate Charge	Q _{G(TH)}		-	0.1	-	nC
Gate-to-Source Charge	Q _{GS}		-	0.15	-	nC
Gate-to-Drain Charge	Q _{GD}		-	0.3	-	nC
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V _{GS} =-4.5V, V _{DS} =-10V , I _D =-450mA R _G =6Ω	-	43	-	nS
Rise Time	tr		-	137	-	nS
Turn-Off Delay Time	td(OFF)		-	1450	-	nS
Fall Time	tf		-	2050	-	nS
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V,I _S =-150mA	-0.5	-0.65	-1.1	V

Note:

1. Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper
2. Surface mounted on FR4 board using minimum pad size, 1oz copper
3. Pulse width < 380 μs , Single pulse
4. Maximum junction temperature $T_J = 150^\circ C$.
5. Pulse test: Pulse width < 380 μs duty cycle < 2%.

Typical Characteristics

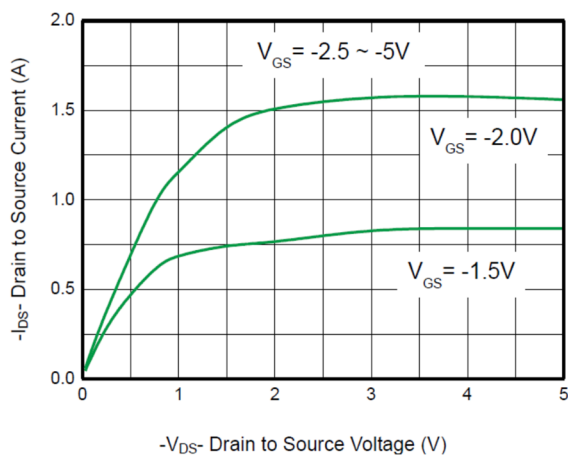


Fig 1. Output characteristics

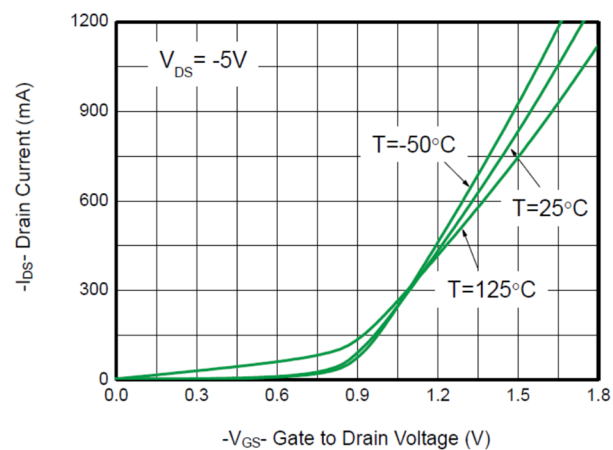


Fig 2. Transfer characteristics

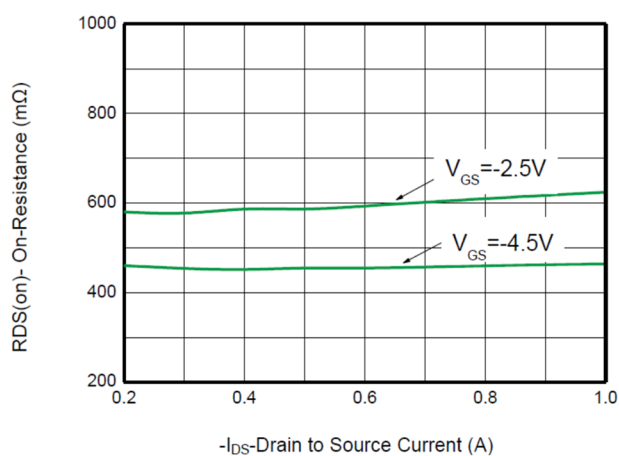


Fig 3. On-Resistance vs. Drain current

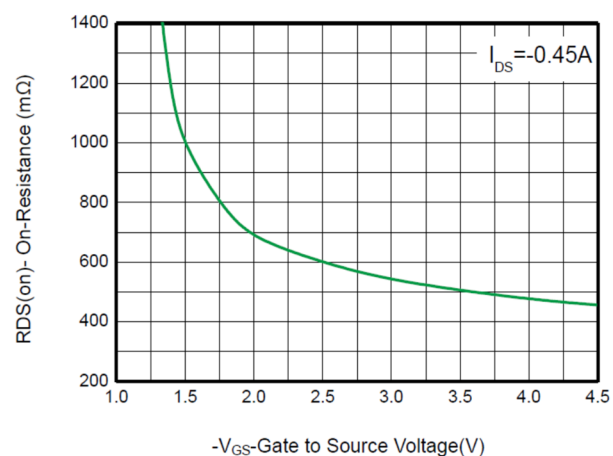


Fig 4. On-Resistance vs. Gate-to-Source voltage

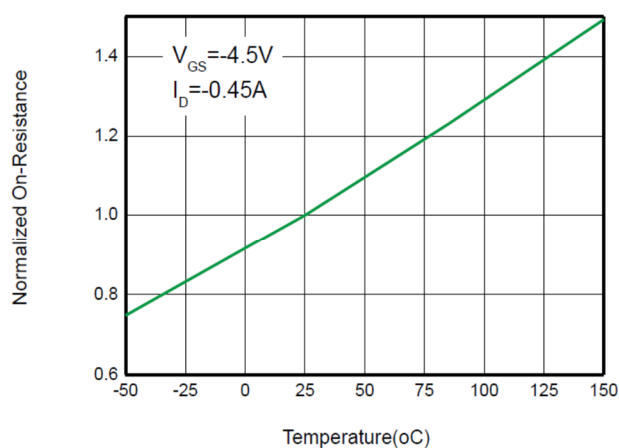


Fig 5. On-Resistance vs. Junction temperature

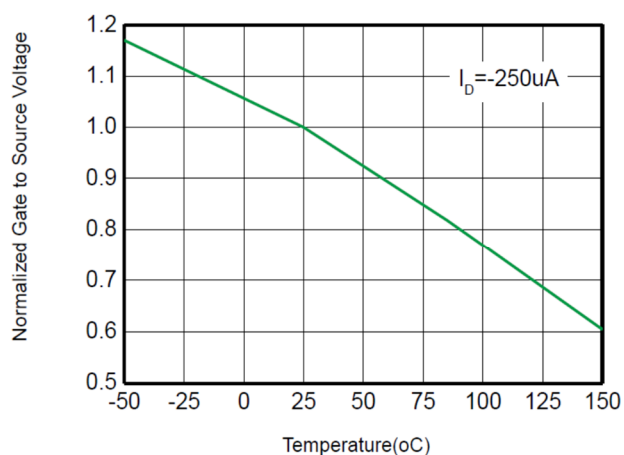


Fig 6. Threshold voltage vs. Temperature

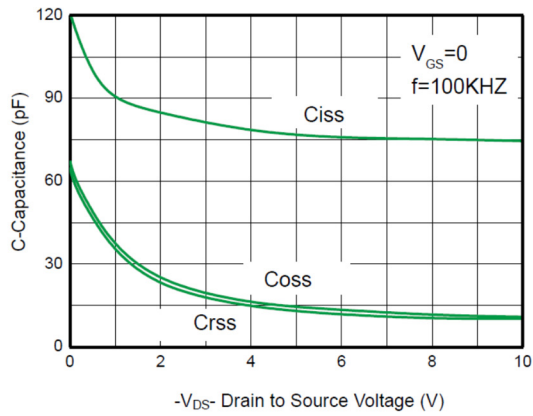


Fig 7. Capacitance.

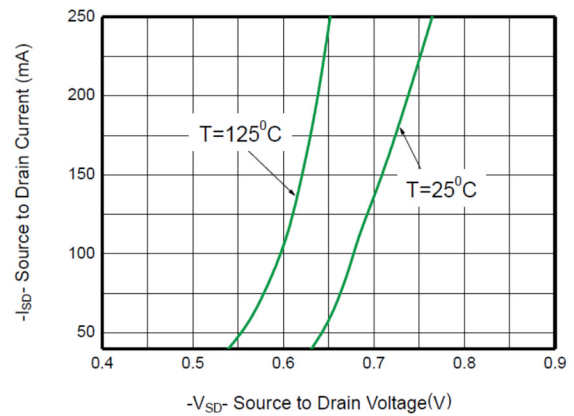
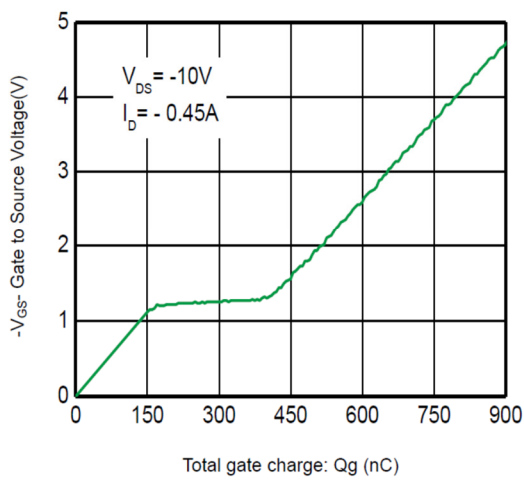
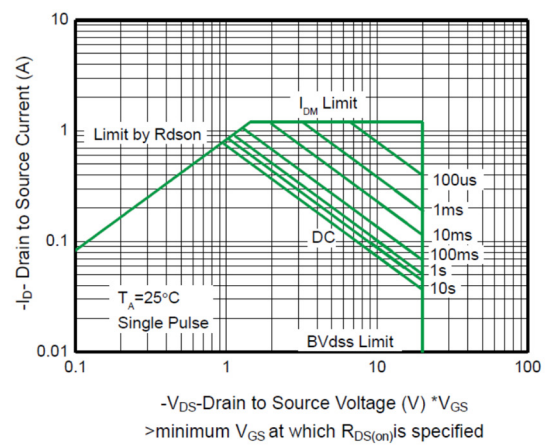
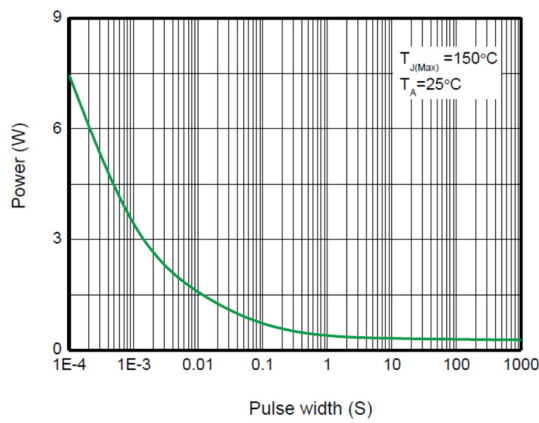
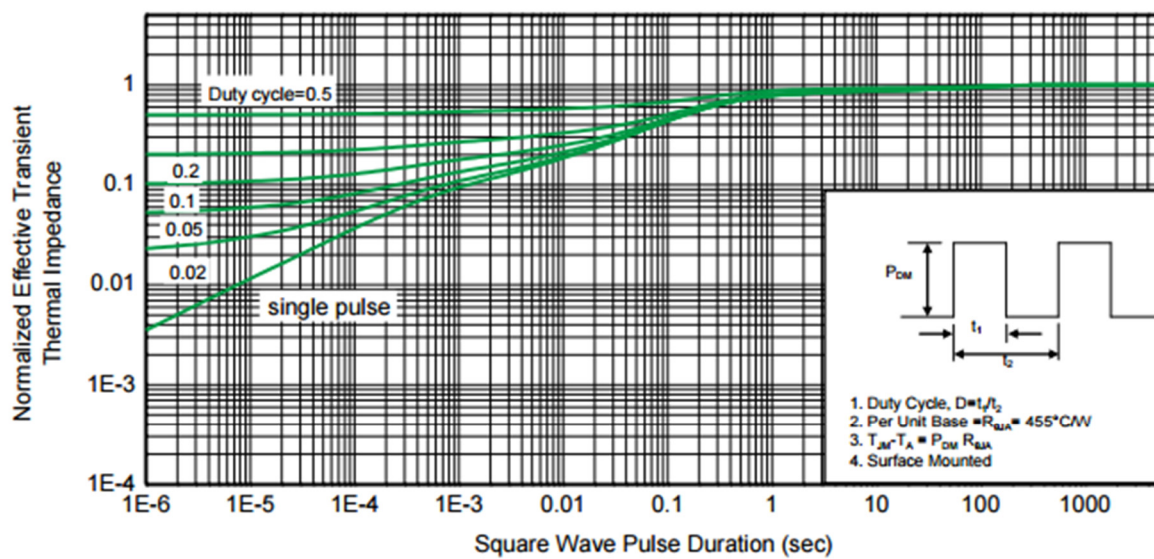


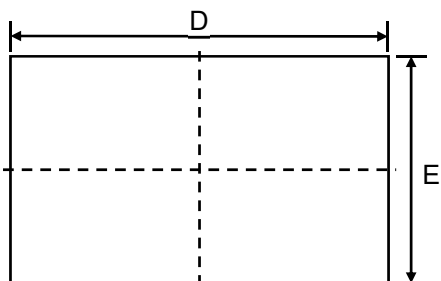
Fig 8. Body diode forward voltage



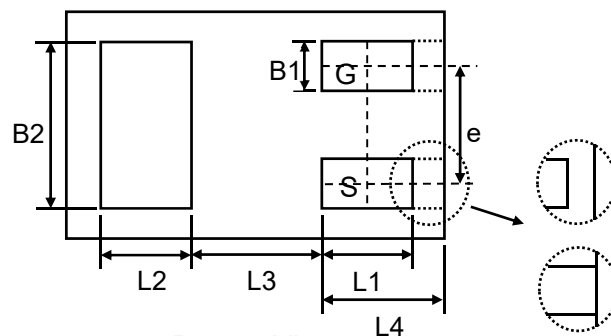


Transient thermal response (Junction-to-Ambient)

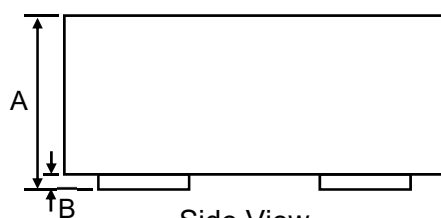
Product dimension (DFN1006-3L)



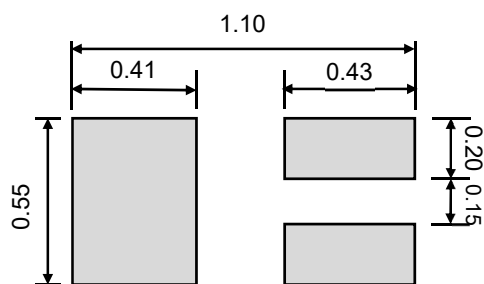
Top View



Bottom View



Side View



Suggested PCB Layout

Unit:mm

Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.33	0.55	0.013	0.022
B	0.00	0.05	0.000	0.002
B1	0.10	0.20	0.004	0.008
B2	0.45	0.55	0.018	0.022
D	0.90	1.05	0.035	0.041
E	0.50	0.65	0.020	0.026
e	0.35		0.014	
L1	0.20	0.30	0.008	0.012
L2	0.20	0.30	0.008	0.012
L3	0.39		0.015	
L4	0.25	0.35	0.010	0.014

Marking information



Ordering information

Device	Package	Reel	Shipping
PPM3FD20V1EN	DFN1006-3L(Pb-Free)	7"	10000 / Tape & Reel

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